## STRUCTURE AND METHOD FOR FORMING A FACETED OPENING AND A LAYER FILLING THEREIN

## ABSTRACT OF THE DISCLOSURE

Structure and method for filling an opening in a semiconductor structure that is less susceptible to the formation of voids. A first layer of a first material is formed over the layer in which the opening is to be formed, and a faceted opening is formed in the first layer. The opening in the underlying layer is subsequently formed, and the material that is to fill the opening is deposited over the faceted opening and into the opening of the underlying layer.

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